

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,022,538 B2
APPLICATION NO. : 10/775894
DATED : April 4, 2006
INVENTOR(S) : Satoshi Inoue

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

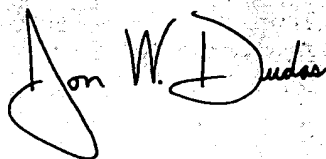
#57

Title Page, Abstract, Lines 1-14:

Delete entire Abstract and insert -- In a manufacturing method in which a source line is provided around a pixel electrode provided on a substrate, an insulating film having open regions that will provide a source and a gate is formed, the source and the drain are formed, and a semiconductor film and a gate are provided on the source and drain, the above constituents are formed substantially under atmospheric pressure. Since manufacture can be accomplished substantially under the atmospheric pressure, no special apparatus, such as a vacuum chamber, is required, permitting a display device to be manufactured at lower cost. --

Signed and Sealed this

Twenty-second Day of August, 2006

A handwritten signature in black ink, appearing to read "Jon W. Dudas", is written over a light, textured background.

JON W. DUDAS
Director of the United States Patent and Trademark Office